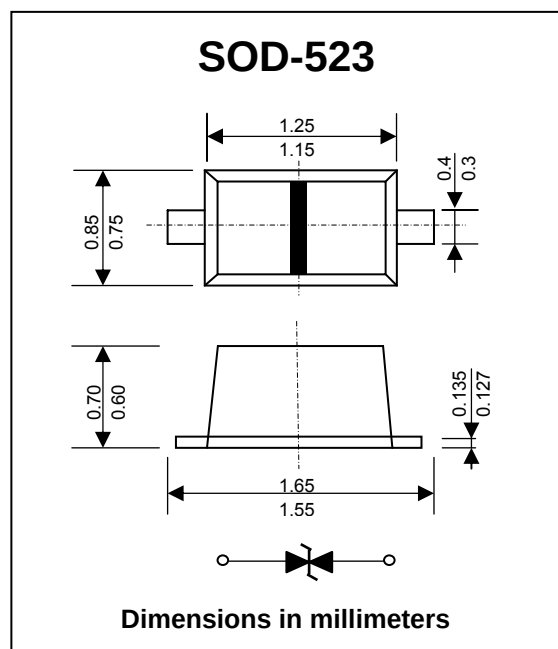


ESD6V8WT

SILICON EPITAXIAL PLANAR DIODE

FEATURES :

- * Bi-direction
- * Ultra small mold type.
- * High reliability
- * Pb / RoHS Free



Absolute Maximum Ratings (Ta = 25 °C)

Parameter	Symbol	Value	Unit
Peak pulse power (tp = 10 x 1000 μs)	P _{PK}	10	W
Power Dissipation	P _D	150	mW
Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55 to + 150	°C

Electrical Characteristics (Ta = 25 °C)

Parameter	Symbol	Min.	Max.	Unit
Zener Voltage at I _Z = 1mA	V _Z	5.5	8.0	V
Reverse Current at V _R = 3.5 V	I _R	-	0.01	μA
Capacitance between terminals at V _R = 0 V, f = 1MHz ,	C _T	-	30	pF
ESD Voltage Capability (Contact Discharge Mode) at Discharge Capacitance / Resistance: 150 pF / 330 Ω	-	-	15	KV
ESD Voltage Capability (Air Discharge Mode) at Discharge Capacitance / Resistance: 150 pF / 330 Ω	-	-	25	KV

RATING AND CHARACTERISTIC CURVES (ESD6V8WT)

